

The FDN359BN uses advanced trench technology

to provide excellent R<sub>DS(ON)</sub>, low gate charge and

operation with gate voltages as low as 2.5V. This

device is suitable for use as a

Battery protection or in other Switching application.



**SOT-23** 

**General Features** 

 $V_{DS} = 30V I_{D} = 5.8A$ 

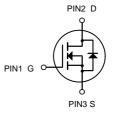
 $R_{DS(ON)}$  < 30m $\Omega$  @  $V_{GS}$ =10V

**Application** 

Battery protection

Load switch

Uninterruptible power supply



N-Channel MOSFET

**Package Marking and Ordering Information** 

| Product ID | Pack   | Marking | Qty(PCS) |
|------------|--------|---------|----------|
| FDN359BN   | SOT-23 | A09T    | 3000     |

#### Absolute Maximum Ratings (T<sub>A</sub>=25 ℃ unless otherwise noted)

| Symbol           | Parameter  | Limit      | Unit       |
|------------------|--|------------|------------|
| VDS              | Drain-Source Voltage                             | 30         | V          |
| V <sub>G</sub> s | Gate-Source Voltage                              | ±12        | ٧          |
| l <sub>D</sub>   | Drain Current-Continuous                         | 5.8        | А          |
| Ідм              | Drain Current-Pulsed (Note 1)                    | 30         | А          |
| P <sub>D</sub>   | Maximum Power Dissipation                        | 1.4        | W          |
| Тл,Твтв          | Operating Junction and Storage Temperature Range | -55 To 150 | $^{\circ}$ |
| Reja             | Thermal Resistance,Junction-to-Ambient (Note 2)  | 89         | °C/W       |

# Electrical Characteristics (T<sub>A</sub>=25°C unless otherwise noted)

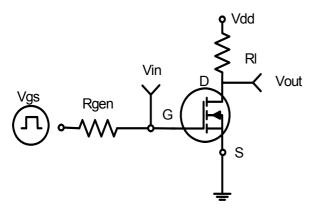
| Parameter                        | Symbol              | Condition                                  | Min | Тур | Max  | Unit |
|----------------------------------|---------------------|--|-----|-----|------|------|
| Drain-Source Breakdown Voltage   | BV <sub>DSS</sub>   | V <sub>GS</sub> =0V I <sub>D</sub> =250μA  | 30  | 33  | -    | V    |
| Zero Gate Voltage Drain Current  | IDSS                | V <sub>DS</sub> =30V,V <sub>GS</sub> =0V   | -   | -   | 1    | μA   |
| Gate-Body Leakage Current        | Igss                | V <sub>GS</sub> =±12V,V <sub>DS</sub> =0V  | -   | -   | ±100 | nA   |
| Gate Threshold Voltage           | V <sub>GS(th)</sub> | $V_{DS}$ = $V_{GS}$ , $I_D$ =250 $\mu$ A   | 0.7 | 0.9 | 1.4  | V    |
|                                  |                     | V <sub>GS</sub> =2.5V, I <sub>D</sub> =4A  | -   | 41  | 55   | mΩ   |
| Drain-Source On-State Resistance | Rds(on)             | V <sub>GS</sub> =4.5V, I <sub>D</sub> =5A  | -   | 32  | 42   | mΩ   |
|                                  |                     | V <sub>GS</sub> =10V, I <sub>D</sub> =5.8A | -   | 28  | 30   | mΩ   |
| Forward Transconductance         | grs                 | V <sub>DS</sub> =5V,I <sub>D</sub> =5A     | 10  | -   | -    | S    |
| Input Capacitance                | Clss                |  | -   | 825 | -    | PF   |
| Output Capacitance               | Coss                | V <sub>DS</sub> =15V,V <sub>GS</sub> =0V,  | -   | 100 | -    | PF   |
| Reverse Transfer Capacitance     | Crss                | F=1.0MHz                                   | -   | 78  | -    | PF   |
| Turn-on Delay Time               | <b>t</b> d(on)      |  | -   | 3.3 | -    | nS   |
| Turn-on Rise Time                | tr                  | $V_{DD}$ =15V, $R_L$ =2.7 $\Omega$         | -   | 4.8 | -    | nS   |
| Turn-Off Delay Time              | td(off)             | $V_{GS}$ =10 $V$ , $R_{GEN}$ =3 $\Omega$   | -   | 26  | -    | nS   |
| Turn-Off Fall Time               | t <sub>f</sub>      |  | -   | 4   | -    | nS   |
| Total Gate Charge                | Qg                  |  | -   | 10  | -    | nC   |
| Gate-Source Charge               | Qgs                 | V <sub>DS</sub> =15V,I <sub>D</sub> =5.8A, | -   | 1.6 | -    | nC   |
| Gate-Drain Charge                | $Q_{gd}$            | V <sub>GS</sub> =4.5V                      | -   | 3.1 | -    | nC   |
| Diode Forward Voltage (Note 3)   | VsD                 | V <sub>GS</sub> =0V,I <sub>S</sub> =5.8A   | -   | -   | 1.2  | V    |
| Diode Forward Current (Note 2)   | Is                  |  | -   | -   | 5.8  | Α    |

#### Notes:

- 1. Repetitive Rating: Pulse width limited by maximum junction temperature.
- **2.** Surface Mounted on FR4 Board,  $t \le 10$  sec.
- **3.** Pulse Test: Pulse Width ≤ 300µs, Duty Cycle ≤ 2%.
- 4. Guaranteed by design, not subject to production



# **Typical Electrical and Thermal Characteristics**



**Figure 1:Switching Test Circuit** 

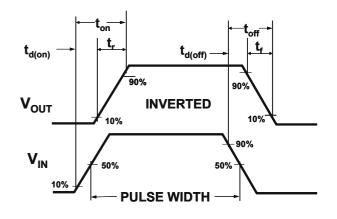
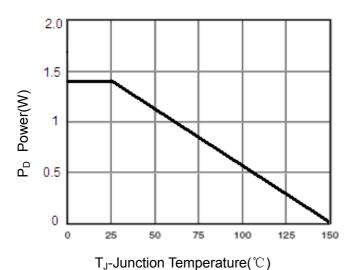


Figure 2:Switching Waveforms



**Figure 3 Power Dissipation** 

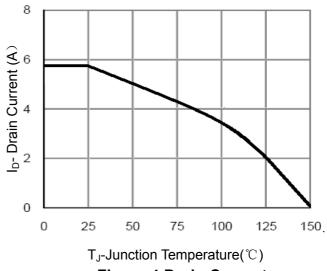
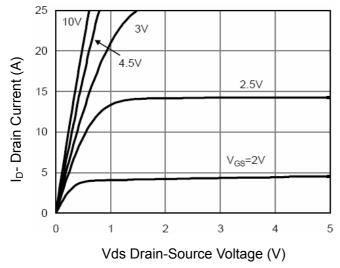


Figure 4 Drain Current



**Figure 5 Output Characteristics** 

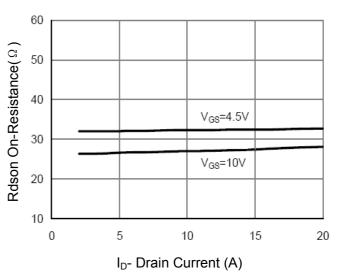
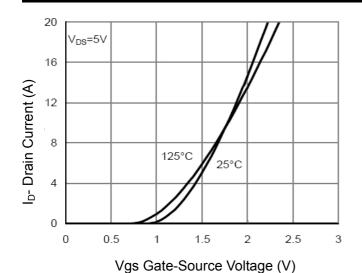
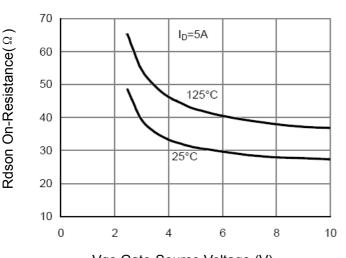


Figure 6 Drain-Source On-Resistance





**Figure 7 Transfer Characteristics** 



Vgs Gate-Source Voltage (V)
Figure 9 Rdson vs Vgs

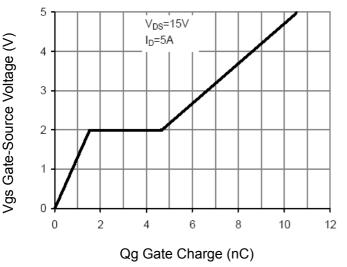


Figure 11 Gate Charge

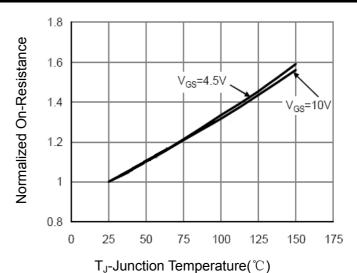


Figure 8 Drain-Source On-Resistance

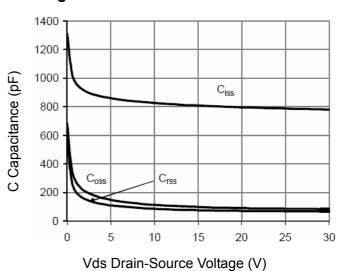


Figure 10 Capacitance vs Vds

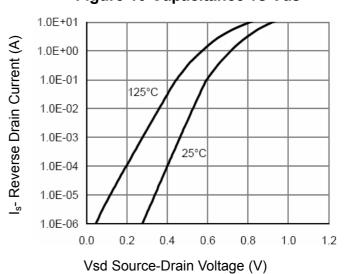
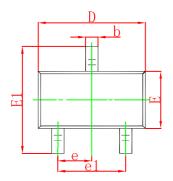
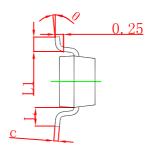
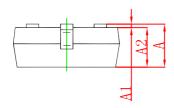


Figure 12 Source- Drain Diode Forward

# **SOT-23 Package Outline Dimensions**

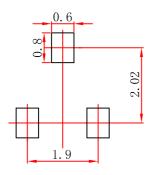






| Symbol | Dimensions In Millimeters |       | Dimensions In Inches |         |  |
|--------|---------------------------|-------|----------------------|---------|--|
|        | Min                       | Max   | Min                  | Max     |  |
| Α      | 0.900                     | 1.150 | 0.035                | 0.045   |  |
| A1     | 0.000                     | 0.100 | 0.000                | 0.004   |  |
| A2     | 0.900                     | 1.050 | 0.035                | 0.041   |  |
| b      | 0.300                     | 0.500 | 0.012                | 0.020   |  |
| С      | 0.080                     | 0.150 | 0.003                | 0.006   |  |
| D      | 2.800                     | 3.000 | 0.110                | 0.118   |  |
| E      | 1.200                     | 1.400 | 0.047                | 0.055   |  |
| E1     | 2.250                     | 2.550 | 0.089                | 0.100   |  |
| е      | 0.950                     | TYP 0 |                      | )37 TYP |  |
| e1     | 1.800                     | 2.000 | 0.071                | 0.079   |  |
| L      | 0.550 REF                 |       | 0.022 REF            |         |  |
| L1     | 0.300                     | 0.500 | 0.012                | 0.020   |  |
| θ      | 0°                        | 8°    | 0°                   | 8°      |  |

# **SOT-23 Suggested Pad Layout**



- Note:
  1.Controlling dimension:in millimeters.
- 2.General tolerance:± 0.05mm.
  3.The pad layout is for reference purposes only.



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